## REMARKS

By this Preliminary Amendment, multiple dependencies in the pending set of claims have been eliminated to avoid additional costs, and claim 25 has been rewritten in dependent form to provide clear antecedent basis for terminology used in that claim.

Entry of this Amendment and favorable consideration of the application are requested.

Respectfully submitted,

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**Version with markings to show changes made.**

4. (Amended) The method of Claim 2 [or 3], wherein an n-doped junction area having heavier doping than that of the trough is produced in the n-doped fringe area of the trough and a p-doped area having heavier doping than that of the p-doped area enclosed by the p-doped inner area is produced in the p-doped area enclosed by the p-doped inner area.

7. (Amended) The method of Claim 5 [or 6], wherein in the n-doped fringe area of the trough an n-doped area having heavier doping than that of the trough and in the n-doped area forming the base an n-doped area having heavier doping than that of the n-doped area forming the base and in the p-doped inner area a p-doped area having heavier doping than that of the p-doped inner area are produced.

15. (Amended) The method of Claim 13[ or 14], wherein an n-doped area having heavier doping than that of the n-doped area forming the gate is inserted into the n-doped area forming the gate.

22. (Amended) The method of [one of Claims 16 to 21] Claim 16, wherein n-doped or p-doped areas for the creation of the structures forming the semiconductor components are produced in the active areas.

25. (Amended) [A] The method of Claim 1 employed for the creation of a structure forming a photosensitive transistor in which an n-doped area is implanted into the p-doped inner area, whereby the terminal forming the collector at the fringe area of the n-doped trough and the terminal forming the emitter at the n-doped area implanted into the p-doped inner area is created.

26. (Amended) The method of [one of Claims 1 to 25] Claim 1, wherein the p-doped or the n-doped semiconductor substrate is a weakly p-doped or n-doped semiconductor substrate.